High Voltage, High Current Darlington Transistor Arrays

The seven NPN Darlington connected transistors in these arrays are well suited for driving lamps, relays, or printer hammers in a variety of industrial and consumer applications. Their high breakdown voltage and internal suppression diodes insure freedom from problems associated with inductive loads. Peak inrush currents to 500 mA permit them to drive incandescent lamps.

The MC1413, B with a 2.7 k Ω series input resistor is well suited for systems utilizing a 5.0 V TTL or CMOS Logic.

Features

• Pb-Free Packages are Available*

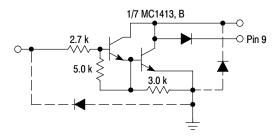


Figure 1. Representative Schematic Diagram

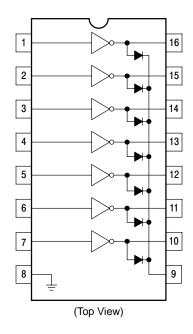


Figure 2. PIN CONNECTIONS



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PDIP-16 P SUFFIX CASE 648



SOIC-16 D SUFFIX CASE 751B

ORDERING INFORMATION

Device	Package	Shipping [†]
MC1413D	SOIC-16	48 Units/Rail
MC1413DR2	SOIC-16	2500 Tape & Reel
MC1413P	PDIP-16	500 Units/Rail
MC1413PG	PDIP-16 (Pb-Free)	500 Units/Tubes
MC1413BD	SOIC-16	48 Units/Rail
MC1413BDR2	SOIC-16	2500 Tape & Reel
MC1413BDR2G	SOIC-16	2500 Tape & Reel
MC1413BP	PDIP-16	500 Units/Rail
NCV1413BDR2	SOIC-16	2500 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 4 of this data sheet.

^{*}For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM RATINGS ($T_A = 25^{\circ}C$, and rating apply to any one device in the package, unless otherwise noted.)

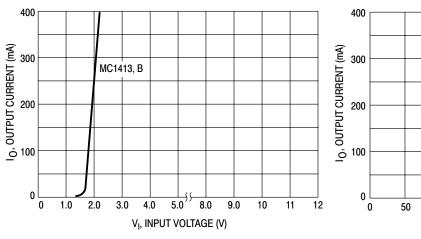
Rating	Symbol	Value	Unit
Output Voltage	Vo	50	V
Input Voltage	VI	30	V
Collector Current – Continuous	I _C	500	mA
Base Current – Continuous	Ι _Β	25	mA
Operating Ambient Temperature Range MC1413 MC1413B NCV1413B	T _A	-20 to +85 -40 to +85 -40 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C
Junction Temperature	TJ	150	°C
Thermal Resistance, Junction-to-Ambient Case 648, P Suffix Case 751B, D Suffix	Rθ _{JA}	67 100	°C/W
Thermal Resistance, Junction-to-Case Case 648, P Suffix Case 751B, D Suffix	Rθ _{JC}	22 20	°C/W
Electrostatic Discharge Sensitivity (ESD) Human Body Model (HBM) Machine Model (MM) Charged Device Model (CDM)	ESD	2000 400 1500	V

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
	I _{CEX}	- -	- -	100 50	μΑ
	V _{CE(sat)}	- - -	1.1 0.95 0.85	1.6 1.3 1.1	V
Input Current – On Condition (V _I = 3.85 V) MC1413, B	I _{I(on)}	-	0.93	1.35	mA
	V _{I(on)}	- - -	- - -	2.4 2.7 3.0	V
Input Current – Off Condition All Types (I $_{C}$ = 500 $_{\mu}A$, T $_{A}$ = 85 $^{\circ}C$)	I _{I(off)}	50	100	-	μΑ
DC Current Gain $(V_{CE} = 2.0 \text{ V}, I_{C} = 350 \text{ mA})$	h _{FE}	1000	-	-	-
Input Capacitance	C _I	_	15	30	pF
Turn-On Delay Time (50% E _I to 50% E _O)	t _{on}	-	0.25	1.0	μs
Turn-Off Delay Time (50% E _I to 50% E _O)	t _{off}	-	0.25	1.0	μs
Clamp Diode Leakage Current $T_A = +25^{\circ}C$ $(V_R = 50 \text{ V})$ $T_A = +85^{\circ}C$	I _R	- -	- -	50 100	μΑ
Clamp Diode Forward Voltage (I _F = 350 mA)	V _F	-	1.5	2.0	V

NOTE: NCV1413B $T_{low} = -40$ °C, $T_{high} = +125$ °C. Guaranteed by design. NCV prefix is for automotive and other applications requiring site and change control.

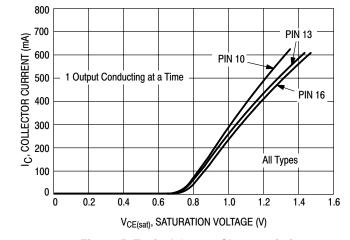
TYPICAL PERFORMANCE CURVES – $T_A = 25$ °C



400 (Ψ) 300 All Types - All Types - 100 100 150 200 250 300 350 400 I_I, INPUT CURRENT (μA)

Figure 3. Output Current versus Input Voltage

Figure 4. Output Current versus Input Current



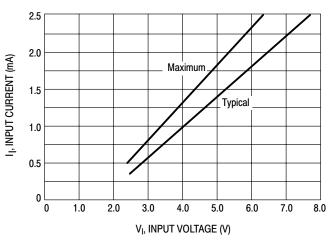


Figure 5. Typical Output Characteristics

Figure 6. Input Characteristics - MC1413, B

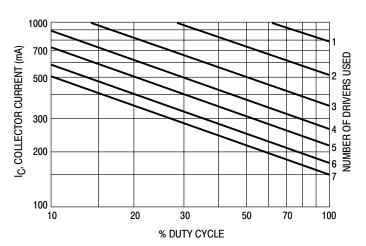
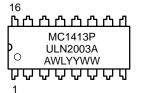
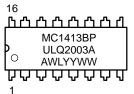


Figure 7. Maximum Collector Current versus Duty Cycle (and Number of Drivers in Use)

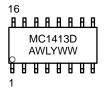
MARKING DIAGRAMS

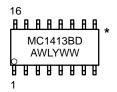
PDIP-16 P SUFFIX CASE 648





SOIC-16 D SUFFIX CASE 751B





A = Assembly Location

WL = Wafer Lot

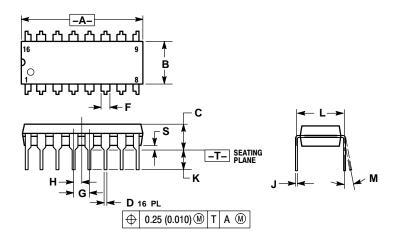
YY, Y = Year

WW = Work Week

^{*}This marking diagram also applies to NCV1413B.

PACKAGE DIMENSIONS

PDIP-16 **P SUFFIX** CASE 648-08 ISSUE R

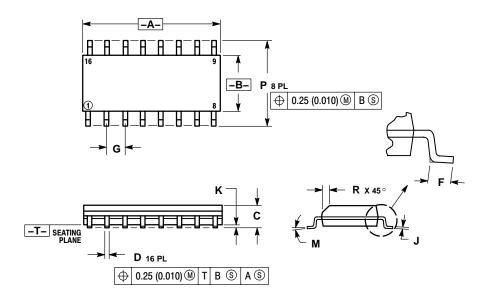


- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
 5. ROUNDED CORNERS OPTIONAL.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.740	0.770	18.80	19.55	
В	0.250	0.270	6.35	6.85	
С	0.145	0.175	3.69	4.44	
D	0.015	0.021	0.39	0.53	
F	0.040	0.70	1.02	1.77	
G	0.100 BSC		2.54 BSC		
Н	0.050	0.050 BSC		1.27 BSC	
J	0.008	0.015	0.21	0.38	
K	0.110	0.130	2.80	3.30	
L	0.295	0.305	7.50	7.74	
M	0°	10 °	0°	10 °	
S	0.020	0.040	0.51	1.01	

PACKAGE DIMENSIONS

SOIC-16 **D SUFFIX** CASE 751B-05 **ISSUE J**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0 °	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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